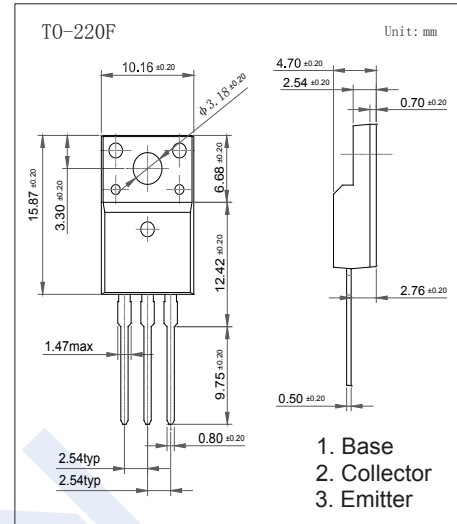


## NPN Transistors

### KTC4370A

■ Features

- High Transition Frequency
- Complementary to KTA1659A



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	180	V
Collector - Emitter Voltage	V <sub>CE0</sub>	180	
Emitter - Base Voltage	V <sub>EB0</sub>	5	
Collector Current - Continuous	I <sub>c</sub>	1.5	A
Base Current	I <sub>B</sub>	0.15	
Collector Power Dissipation T <sub>c</sub> = 25°C	P <sub>c</sub>	20	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = 100uA, I <sub>E</sub> = 0	180			V
Collector- emitter breakdown voltage	V <sub>CE0</sub>	I <sub>c</sub> = 10 mA, I <sub>B</sub> =0	180			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = 100uA, I <sub>c</sub> = 0	5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = 180V, I <sub>E</sub> = 0			1	uA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = 5V, I <sub>c</sub> =0			1	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =500mA, I <sub>B</sub> =50mA			1.5	V
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =500mA, I <sub>B</sub> =50mA			1.2	
Base - emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = 5V, I <sub>c</sub> =500mA			1	
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5V, I <sub>c</sub> =100mA	70		240	
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> =0, f=1MHz		25		pF
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>c</sub> = 100mA		100		MHz

■ Classification of h<sub>FE</sub>

Type	KTC4370A-O	KTC4370A-Y
Range	70-140	120-240